

DSAF00500L

Silicon PNP epitaxial planar type

For general amplification

Complementary to DSCF005

DSA3005 in ML3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: A3

■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	-60	V
Collector-emitter voltage (Base open)	VCEO	-50	V
Emitter-base voltage (Collector open)	VEBO	-6	V
Collector current	IC	-200	mA
Peak collector current	ICp	-300	mA
Collector power dissipation ^{*1}	Pc	100	mW
Junction temperature	Tj	150	$^{\circ}\text{C}$
Storage temperature	Tstg	-55 to +150	$^{\circ}\text{C}$

Note) *1: Copper plate at the collector is 5.0 mm^2 on substrate at $10 \times 12 \times 0.8\text{ mm}$.

■ Electrical Characteristics $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	VCEO	IC = -100 μA , IB = 0	-50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = -60 V, IE = 0			-0.1	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = -6 V, IC = 0			-0.1	μA
Forward current transfer ratio	h_{FE1}	VCE = -6 V, IC = -1mA	150		390	-
Forward current transfer ratio	h_{FE2}	VCE = -6 V, IC = -0.1mA	90			-
Collector-emitter saturation voltage	VCE(sat)	IC = -100 mA, IB = -10 mA			-0.3	V
Transition frequency	fT	VCE = -6 V, IC = -10 mA		150		MHz
Collector output capacitance (Common base, input open circuited)	Cob	VCB = -6 V, IE = 0, f = 1 MHz		5.0		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

